DAA200XA1800NA

=

Ξ

 V_{RRM}

I _{fav}

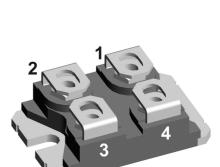
VF

Avalanche Rectifier

Anti-parallel legs

Part number

DAA200XA1800NA

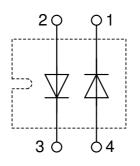


Backside: isolated **E**72873

1800 V

1.21 V

= 2x 100 A



Features / Advantages:

- Avalanche rated
- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase
- bridge configurations

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper
- internally DCB isolated
- Advanced power cycling

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you. Should you intend to use the product in aviation, in health or live endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747and per semiconductor unless otherwise specified

20160412a

LIXYS

DAA200XA1800NA

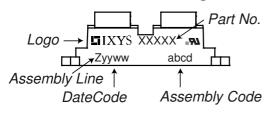
Rectifier	Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse block	ing voltage	$T_{VJ} = 25^{\circ}C$			1900	V	
V _{RRM}	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			1800	V	
I _R	reverse current	V _R = 1800 V	$T_{VJ} = 25^{\circ}C$			200	μA	
		$V_{R} = 1800 V$	$T_{VJ} = 150^{\circ}C$			2	mA	
V _F	forward voltage drop	I _F = 100 A	$T_{VJ} = 25^{\circ}C$			1.24	V	
		I _F = 200 A				1.55	V	
		$I_{F} = 100 \text{ A}$	T _{VJ} = 125 °C			1.21	V	
		$I_{F} = 200 \text{ A}$				1.61	V	
FAV	average forward current	T _c = 100°C	T _{vJ} = 150°C			100	Α	
		rectangular d = 0.5						
V _{F0}	threshold voltage		T _{vj} = 150°C			0.80	V	
r _F	slope resistance } for power lo	oss calculation only				4	mΩ	
R _{thJC}	thermal resistance junction to cas	e				0.3	K/W	
R _{thCH}	thermal resistance case to heatsi	nk			0.10		K/W	
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			415	W	
	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{vJ} = 45^{\circ}C$			1.50	kA	
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			1.62	kA	
		t = 10 ms; (50 Hz), sine	T _{vj} = 150°C			1.28	kA	
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			1.38	kA	
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			11.3	kA²s	
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			10.9	kA²s	
		t = 10 ms; (50 Hz), sine	T _{vj} = 150°C			8.13	kA²s	
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			7.87	kA²s	
C	junction capacitance	V_{R} = 400 V; f = 1 MHz	$T_{VJ} = 25^{\circ}C$		53		pF	
P _{RSM}	max. surge reverse dissipation	t _p = 10 μs	T _{v.i} = 150°C			20	kW	

20160412a

DAA200XA1800NA

Package SOT-227B (minibloc)				Ratings				
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					150	Α
T _{vj}	virtual junction temperature				-40		150	°C
T _{op}	operation temperature				-40		125	°C
T _{stg}	storage temperature						150	°C
Weight						30		g
M _D	mounting torque				1.1		1.5	Nm
M _T	terminal torque				1.1		1.5	Nm
d _{Spp/App}	creepage distance on surface striking distance through air		terminal to terminal	10.5	3.2			mm
d _{Spb/Apb}	creepage distance on surface s	unking distance unough an	terminal to backside	8.6	6.8			mm
V	isolation voltage	t = 1 second			3000			V
		t = 1 minute	50/60 Hz, RMS; liso∟ ≤ 1 mA		2500			V

Product Marking



Part description

- D = Diode A = Avalanche Rectifier
- A = (up to 1800V)
- 200 = Current Rating [A] XA = Anti-parallel legs
- 1800 = Reverse Voltage [V]
- NA = SOT-227B (minibloc)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DAA200XA1800NA	DAA200XA1800NA	Tube	10	517661

Similar Part	Package	Voltage class
DAA200X1800NA	SOT-227B (minibloc)	1800
DMA200X1600NA	SOT-227B (minibloc)	1600
DMA200XA1600NA	SOT-227B (minibloc)	1600

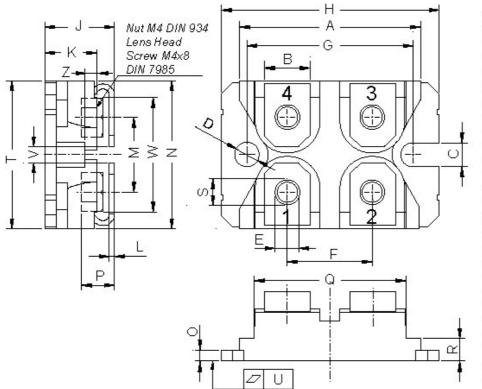
Equiva	alent Circuits for	Simulation	* on die level	$T_{VJ} = 150 \text{ °C}$
)[R	Rectifier		
V _{0 max}	threshold voltage	0.8		V
$\mathbf{R}_{0 \max}$	slope resistance *	2.2		mΩ

IXYS reserves the right to change limits, conditions and dimensions.

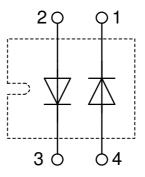
20160412a



Outlines SOT-227B (minibloc)



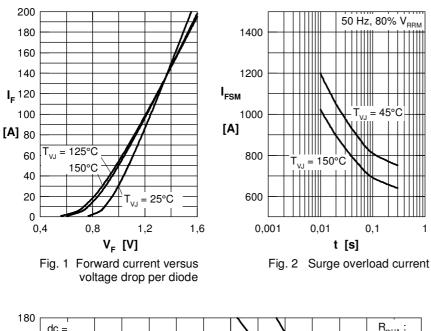
Dim	Millir	neter	Inches		Inches	
Dini.	min	max	min	max		
Α	31.50	31.88	1.240	1.255		
в	7.80	8.20	0.307	0.323		
С	4.09	4.29	0.161	0.169		
D	4.09	4.29	0.161	0.169		
Е	4.09	4.29	0.161	0.169		
F	14.91	15.11	0.587	0.595		
G	30.12	30.30	1.186	1.193		
Н	37.80	38.23	1.488	1.505		
J	11.68	12.22	0.460	0.481		
К	8.92	9.60	0.351	0.378		
L	0.74	0.84	0.029	0.033		
М	12.50	13.10	0.492	0.516		
Ν	25.15	25.42	0.990	1.001		
0	1.95	2.13	0.077	0.084		
Р	4.95	6.20	0.195	0.244		
Q	26.54	26.90	1.045	1.059		
R	3.94	4.42	0.155	0.167		
S	4.55	4.85	0.179	0.191		
Т	24.59	25.25	0.968	0.994		
U	-0.05	0.10	-0.002	0.004		
V	3.20	5.50	0.126	0.217		
W	19.81	21.08	0.780	0.830		
Ζ	2.50	2.70	0.098	0.106		

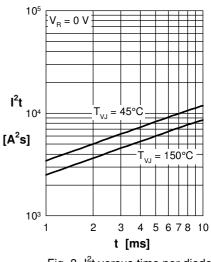


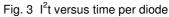
IXYS reserves the right to change limits, conditions and dimensions.

DAA200XA1800NA

Rectifier







dc =

0.5

0.4

0.33

0.17

0.08

100 125 150

T_c [°C]

versus case temperature

t_i (s)

20160412a

Fig. 5 Max. forward current

Constants for Z_{thJC} calculation:

240

200

160

120

80

40

0

i

0 25 50 75

I_{F(AV)M}

[A]

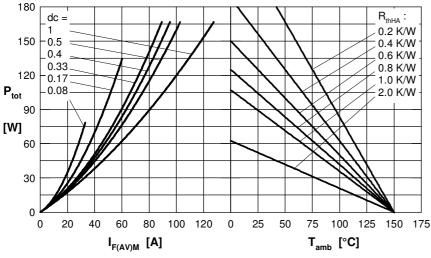
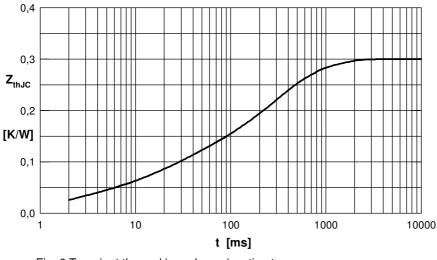


Fig. 4 Power dissipation vs. direct output current & ambient temperature



R_{thi} (K/W) 1 0.025 0.011

> 2 0.027 0.002 3 0.048 0.027

4 0.080 0.600 5 0.120 0.220



IXYS reserves the right to change limits, conditions and dimensions.